| Form PTO-1449 (Modified) | 7011-2 | Atty. Docket No. 50422-8 | Serial No. 10/761,409 |
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| LIST OF PATENTS AND PUBLICATI FOR APPLICANT'S INFORMATION | 1111 1000 1 | Applicant Steven E. Hill | <u> </u> |
| DISCLOSURE STATEMENT (Use several sheets if necessary) | וייטני מו | Filing Date January 22, 2004 | Group 2812 |

REFERENCE DESCRIPTION U.S. PATENT DOCUMENTS

| EXAM. INIT. | | | DOCUMENT NUMBER | | | DATE | NAME | CLASS | SUB CLASS | FIL.DATE IF APPROPRIATE | | | |
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